MA4SW410B-1



HMIC™ Silicon PIN Diode Switch with Integrated Bias Network

Rev. V4

Features

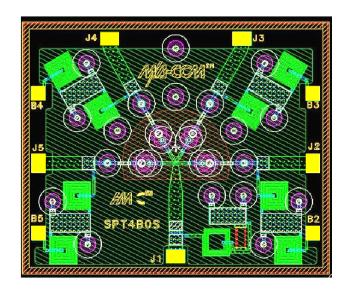
- Broad Bandwidth Specified up to 18 GHz
- Usable up to 26 GHz
- Integrated Bias Network
- Low Insertion Loss / High Isolation
- Rugged, Glass Encapsulated Construction
- **Fully Monolithic**
- RoHS Compliant* and 260°C Reflow Compatible

Description

The MA4SW410B-1 device is a SP4T broadband switch with integrated bias network utilizing M/A-COM Technology Solutions HMIC[™] (Heterolithic Microwave Integrated Circuit) process, US Patent 5,268,310. This process allows the incorporation of silicon pedestals that form series and shunt diodes or vias by imbedding them in low loss, low dispersion glass. By using small spacing between elements, this combination of silicon and glass gives HMIC devices low loss and high isolation performance with exceptional repeatability through low millimeter frequencies. Large bond pads facilitate the use of low inductance ribbon bonds, while gold backside metallization allows for manual or automatic chip bonding via 80/20 - Au/Sn, 62/36/2 - Sn/Pb/Ag solders or electrically conductive silver epoxy.

Applications

These high performance switches are suitable for use in multi-band ECM, Radar, and instrumentation control circuits where high isolation to insertion loss ratios are required. With a standard +5V/-5V, TTL controlled PIN diode driver, 80nS switching speeds can be achieved.



Yellow areas denote wire bond pads

Parameter	Absolute Maximum		
Operating Temperature	-65°C to +125°C		
Storage Temperature	-65°C to +150°C		
Junction Temperature	+175°C		
Applied Reverse Voltage	50V		
RF Incident Power	+30dBm C.W. ¹		
Bias Current +25°C	± 40mA		

Note:

1. Maximum operating conditions for combination of RF power, D.C. bias and temperature:

^{*} Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

[•] India Tel: +91.80.43537383 • China Tel: +86.21.2407.1588 Visit www.macomtech.com for additional data sheets and product information.



Rev. V4

MA4SW410B-1 (SP4T) Electrical Specifications @ T_{AMB} = +25°C, 10mA Bias current

Parameter	Frequency	Minimum	Nominal	Maximum	Units
Insertion Loss	6 GHz	-	0.80	1.0	dB
	12 GHz	-	1.00	1.2	dB
	18 GHz	-	1.40	1.6	dB
Isolation	6 GHz	40	50	-	dB
	12 GHz	35	40	-	dB
	18 GHz	30	35	-	dB
Input Return Loss	6 GHz	-	10	-	dB
	12 GHz	-	15	-	dB
	18 GHz	-	10	-	dB
Switching Speed ¹	-	-	80	-	ns

Note:

Operation of the MA4SW410B-1

Operation of the HMIC Series of PIN switches is achieved by the simultaneous application of negative DC current to the low loss port and positive DC current to the remaining isolated switching ports per the Driver Connections table below. The control currents should be supplied by constant current sources. For insertion loss, -10mA bias results in approximately -2V, and for Isolation ,+10mA yields approximately +0.9V at the respective bias nodes. The backside area of the die is the RF and DC return ground plane.

Driver Connections

CONTROL LEVEL (DC CURRENT)			CONDITION OF RF OUTPUT				
B2	B3	B4	B5	J1-J2	J1-J3	J1-J4	J1-J5
-10mA	+10mA	+10mA	+10mA	Low Loss	Isolation	Isolation	Isolation
+10mA	-10mA	+10mA	+10mA	Isolation	Low Loss	Isolation	Isolation
+10mA	+10mA	-10mA	+10mA	Isolation	Isolation	Low Loss	Isolation
+10mA	+10mA	+10mA	-10mA	Isolation	Isolation	Isolation	Low Loss

^{1.}Typical switching speed measured from 10% to 90% of detected RF signal driven by TTL compatible drivers using RC output spiking network, $R = 50 - 200\Omega$, C = 390 - 560pF.

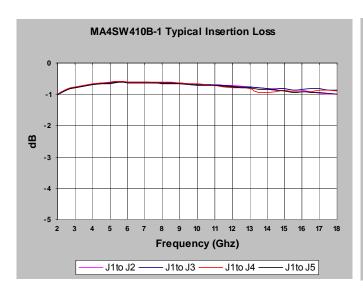
[•] India Tel: +91.80.43537383 • China Tel: +86.21.2407.1588

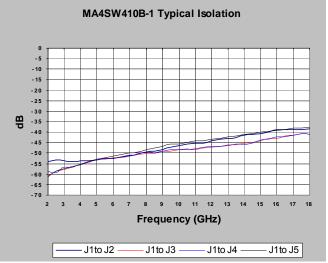
Visit www.macomtech.com for additional data sheets and product information.

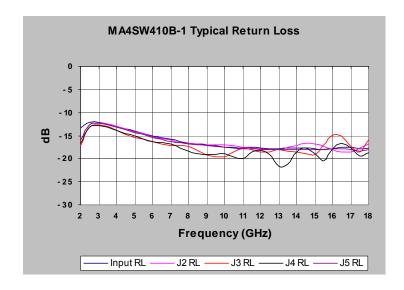


Rev. V4

Typical RF Performance @ T_{AMB} = +25°C (Probed on Wafer)





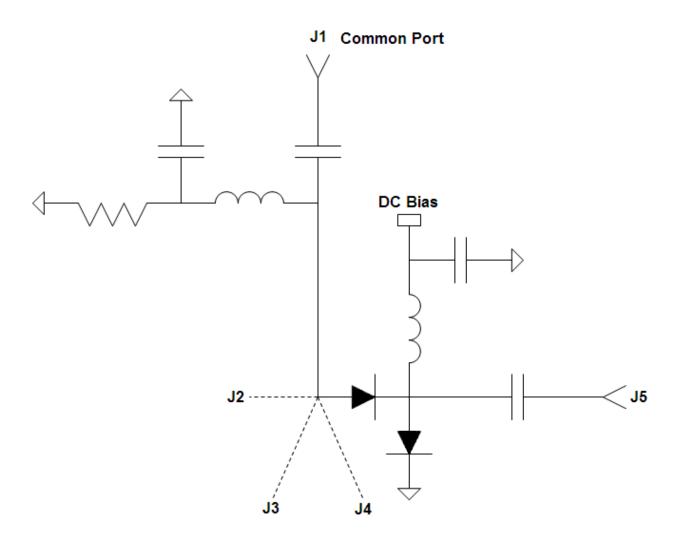


India Tel: +91.80.43537383
 China Tel: +86.21.2407.1588
 Visit www.macomtech.com for additional data sheets and product information.



Rev. V4

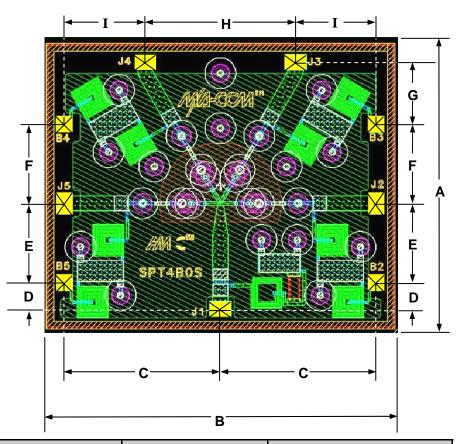
MA4SW410B-1 Schematic





Rev. V4

MA4SW410B-1 Chip Outline Drawing^{1,2}



DIM	M	ils	Millimeters		
DIN	MIN	MAX	MIN	MAX	
Α	85	89	2.17	2.27	
В	106	110	2.69	2.79	
С	48	52	1.22	1.32	
D	7	11	0.17	0.27	
Е	33	34	0.85	0.86	
F	57	61	1.46	1.56	
G	77	81	1.96	2.06	
Н	46	50	1.18	1.28	
I	24	28	0.61	0.71	
RF Bond Pads (J1-J6)	7 X 5 REF.		.178 X .127 REF.		
DC Bond Pads (B2-B5)	5 X 5 REF.		.127 X .1	27 REF.	
Chip Thickness	5 REF.		0.127 REF.		

Notes:

1. Topside and backside metallization is gold , 2.5 μM thick typical.



Rev. V4

Wire/Ribbon and Die Attachment Recommendations

Cleanliness

These chips should be handled in a clean environment.

Wire Bonding

Thermosonic wedge wire bonding using 0.00025" x 0.003" ribbon or 0.001" diameter gold wire is recommended. A heat stage temperature of 150°C and a force of 18 to 22 grams should be used. Ultrasonic energy should be adjusted to the minimum required to achieve a good bond. RF bond wires should be kept as short and straight as possible.

Mounting

The HMIC switches have Ti-Pt-Au back metal. They can be die mounted with a gold-tin eutectic solder preform or conductive epoxy. Mounting surface must be clean and flat.

*Note: This device utilizes a process step designed to have minimal to non-existent burring around the perimeter of the die.

Eutectic Die Attachment

An 80/20, gold-tin, eutectic solder preform is recommended with a work surface temperature of 255°C and a tool tip temperature of 265°C. When hot gas is applied, the tool tip temperature should be 290°C. The chip should not be exposed to temperatures greater than 320°C for more than 20 seconds. No more than three seconds should be required for attachment. Solders containing tin should not be used.

Epoxy Die Attachment

Commitment to produce in volume is not guaranteed

A minimum amount of epoxy should be used. A thin epoxy fillet should be visible around the perimeter of the chip after placement. Cure epoxy per manufacturer's schedule. (typically 125-150°C).

Ordering Information

Part Number	Package
MA4SW410B-1	Gel Pack (25 Per)
MASW-004102-12760W	Waffle Pack (25 Per)

typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available.



OOO «ЛайфЭлектроникс" "LifeElectronics" LLC

ИНН 7805602321 КПП 780501001 P/C 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 3010181090000000703 БИК 044030703

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный) Email: org@lifeelectronics.ru